PJX86	603-AU				
ompleme	ntary Enhan	cement Mod	e MOSFET – I	ESD Protected	
Voltage	50 / -60V	Current	0.36A / -0.2A	SOT-563	
Features					
Advanced	Trench Process	Technology			
Specially D	Designed for Swi	tch Load, PWM	Application, etc		
ESD Prote	cted 2KV HBM				
AEC-Q101	qualified				
Lead free i	n compliance wi	th EU RoHS 2.0)		
Green mol	ding compound	as per IEC6124	9 standard		
				D1	
Mechanic	al Data			6	
Case : SOT	-563 Package				_{╣└╼┙} ╘┙╪╷
Terminals :	Solderable per MI	L-STD-750, Meth	od 2026		₩ ₩
		ices, 0.0026 gram			

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage	V _{DS}	50	-60		
Gate-Source Voltage	V _{GS}	<u>+</u> 20	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	I _D	360	-200	mA	
Pulsed Drain Current ^(Note 1)	Ідм	1200	-900		
	Ta=25°C		300		mW
Power Dissipation	Derate above 25°C	- P _D	2.4		mW/∘C
Operating Junction and Storage Tem	TJ,TSTG	-55~150		°C	
Typical Thermal Resistance - Junction to Ambient ^(Note 3,4)		Reja	417		°C/W





N-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static		·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D = 250uA	50	-	-	v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.5	0.9	1	V	
	R _{DS(on)}	V _{GS} = 10V, I _D = 500mA	-	1.26	1.5		
Drain-Source On-State Resistance		V_{GS} = 4.5V, I _D = 200mA	-	1.34	2.5	Ω	
Zero Gate Voltage Drain Current	I _{DSS}	I _{DSS} V _{DS} = 50V, V _{GS} =0V		-	1		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 10	uA	
Dynamic ^(Note 5)							
Total Gate Charge	Qg		-	0.95	-	nC	
Gate-Source Charge	Q _{gs}	$V_{DS}=25V, I_{D}=500mA,$	-	0.34	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5V	-	0.32	-		
Input Capacitance	Ciss		-	36	-	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	11	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	6.6	-		
Turn-On Delay Time	td _(on)		-	2.3	-		
Turn-On Rise Time	tr	$V_{DD}=25V, I_{D}=500mA,$	-	20	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V$,	-	7	-	ns	
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note 1,2)}$	-	20	-		
Drain-Source Diode							
Maximum Continuous Drain-Source					200		
Diode Forward Current	ls		-	-	360	mA	
Diode Forward Voltage	V _{SD}	Is= 500mA, V _{GS} =0V	-	0.9	1.5	V	

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





P-Channel Electrical Characteristics (T_A=25°C unless otherwise noted)

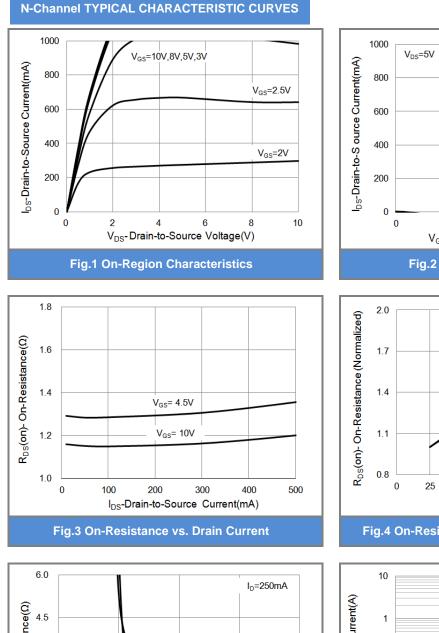
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V, I _D =-250uA		-60	-	-	v
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.5	-2.5	v
Drain Source On State Desistance		V _{GS} =-10V, I _D =-500mA	-	2.6	6	0
Drain-Source On-State Resistance	RDS(on)	V _{GS} =-4.5V, I _D =-200mA	-	2.9	7	Ω
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-48V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	lgss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 5)						
Total Gate Charge	Qg		-	1.1	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-25V, I _D =-100mA,	-	0.3	-	
Gate-Drain Charge	Q_{gd}	V _{GS} =-4.5V	-	0.2	-	
Input Capacitance	Ciss		-	51	-	pF
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V,	-	15	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	2.2	-	
Turn-On Delay Time	td _(on)		-	4.8	-	
Turn-On Rise Time	tr	V_{DD} =-25V, I _D =-100mA,	-	19	-	
Turn-Off Delay Time	td _(off)	V _{GS} =-10V,	-	52	-	ns
Turn-Off Fall Time	tf	$R_G=6\Omega^{(Note 1,2)}$	-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					200	
Diode Forward Current	ls		-	-	-200	mA
Diode Forward Voltage	V _{SD}	Is=-500mA, V _{GS} =0V	-	-0.9	-1.5	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.







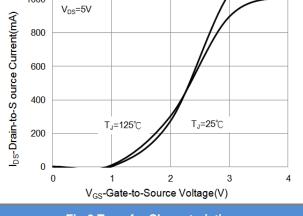


Fig.2 Transfer Characteristics

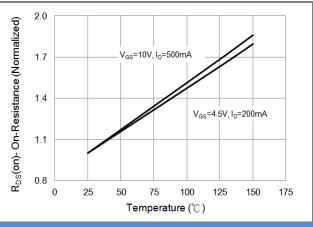
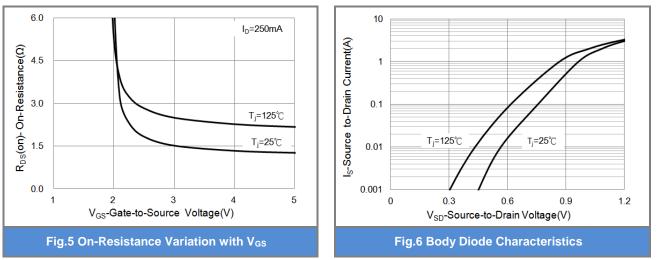
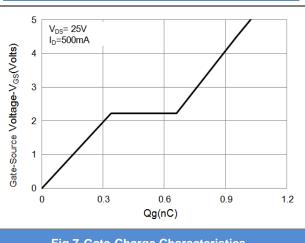


Fig.4 On-Resistance vs. Junction temperature







N-Channel TYPICAL CHARACTERISTIC CURVES

Fig.7 Gate-Charge Characteristics

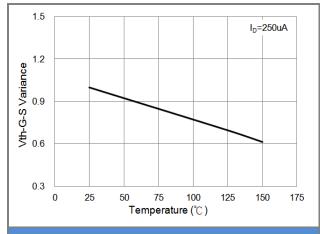
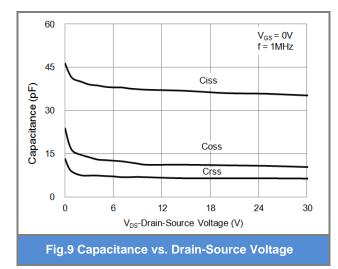
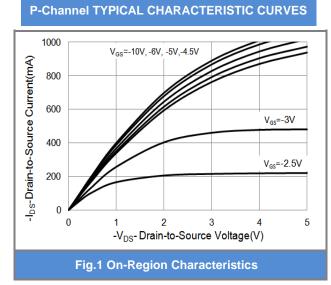


Fig.8 Threshold Voltage Variation with Temperature



ΡΛΝ	JIT
	SEMI
	CONDUCTOR





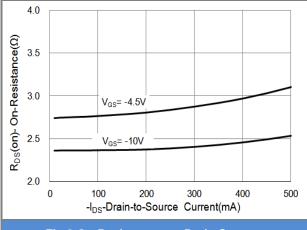
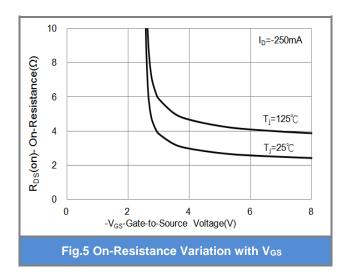


Fig.3 On-Resistance vs. Drain Current



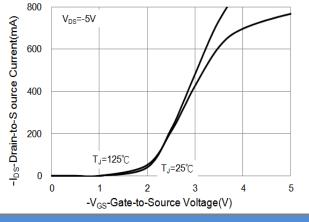


Fig.2 Transfer Characteristics

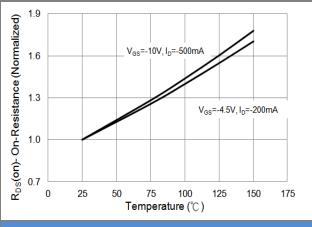
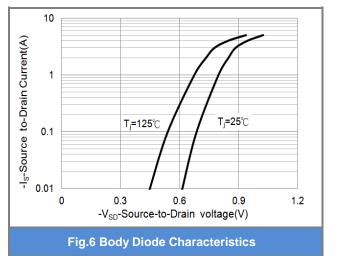
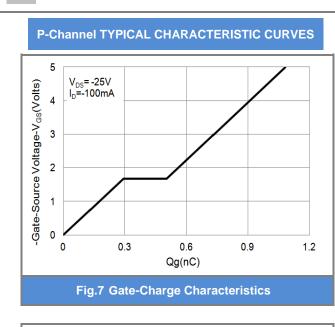


Fig.4 On-Resistance vs. Junction temperature



December 9,2021



Coss

-V_{DS}-Drain-Source Voltage (V)

24

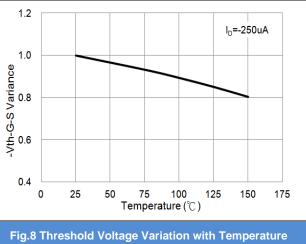
32

16

Fig.9 Threshold Voltage Variation with Temperature

3 0.6 0.9 1.2 Qg(nC) 0.4 0 25 50 e-Charge Characteristics T Fig.8 Threshold Voltage

40



80

60

40

20

0 Crss 0

8

Capacitance (pF)

PJX8603-AU



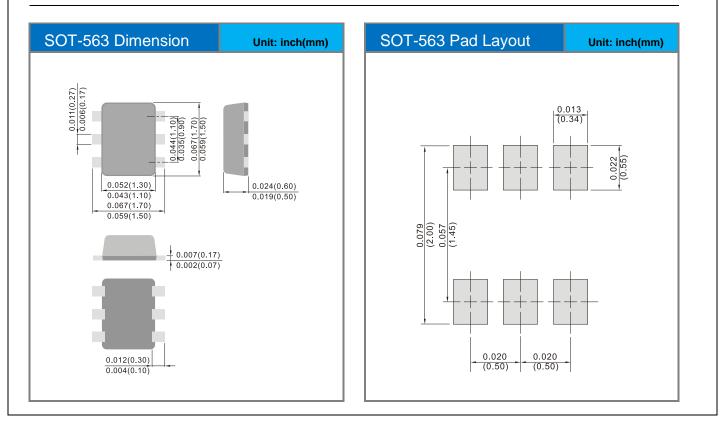




Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJX8603-AU_R1_000A1	SOT-563	4K pcs / 7" reel	X63	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout





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